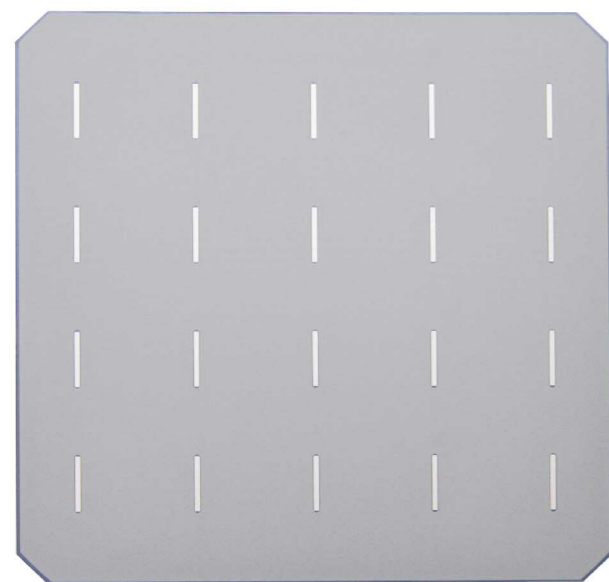


HIGH-EFFICIENCY ANTI-PID MONO CELLS (5BB)

Fullstar uses high-efficiency mono crystalline cells it has become easier than ever to manufacture modules with more than 295Wp (6*10) and 345Wp (6*12) power output. Meanwhile the anti-PID cell technology reduces the module attenuation caused by induced electric potential, as well as system power attenuation caused by the high temperature, humidity and salty atmosphere.



The module adopts the non-anti-PID EVA, 85°C, 96H, -1000V, and leads the Attenuation

≤ 2%

Advantage

- ◆ The advanced flocking additives cleaning technology for silicon system makes the surface of silicon uniformly, also reflection is reduced.
- ◆ The unique expansion technology ensure the uniformity.
- ◆ The advanced PECVD technology makes the dark blue silicon nitride antireflection film uniform and beautiful color.
- ◆ High quality metal paste for back field and electrode, ensuring excellent electrical conductivity, reliable adhesion and wonderful weldability.
- ◆ Low breakage ratio, high excellent quality ratio.
- ◆ Rigorous standards for classification and bus bar design, decreasing the possibility of power dissipation during assembling process.

Mechanical Data And Design

Format	156S M1 M2 M3 160S
Thickness	200±20 μm
Front (-)	5*0.7mm±0.1mm bus bars(silver).blue anti-reflecting coating(silicon nitride)
Back (+)	5*1.8mm wide soldering pads(silver) back surface field (aluminum)

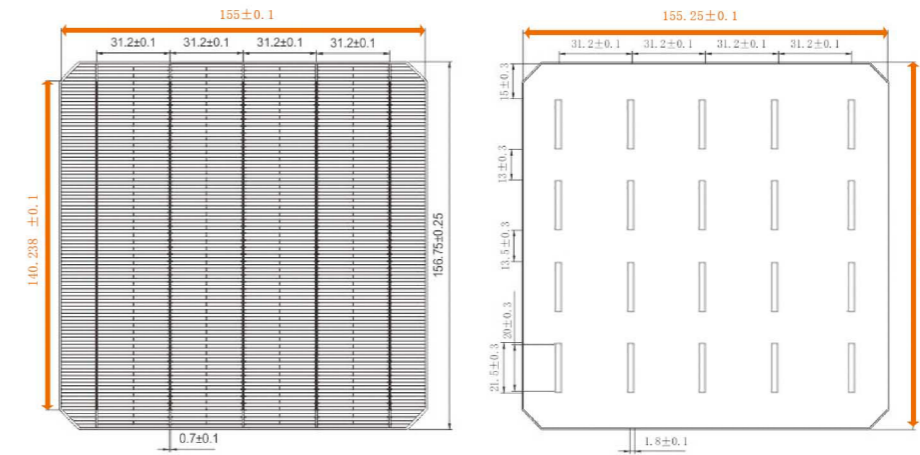
Temperature Coefficients

Tk voltage	-0.36%/k
Tk current	+0.07%/k
Tk power	-0.38%/k

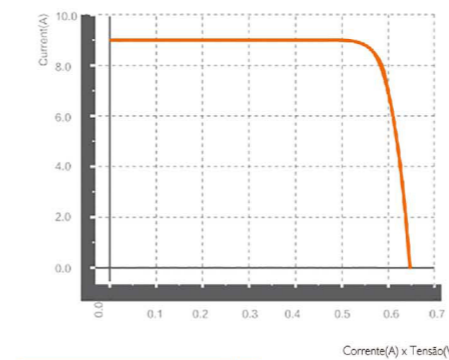
The explanation of sizes

Format	Side(mm)	Diagonal(mm)
156S	156.00	R200
M1	156.75	R205
M2	156.75	R210
M3	156.75	R205
160S	160.00	R200

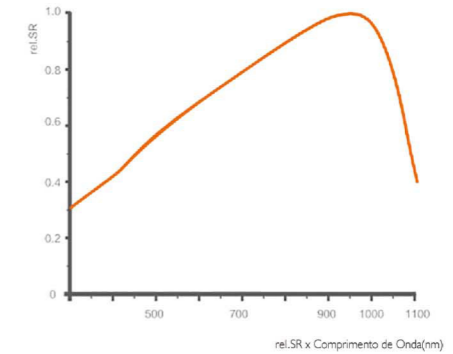
Size



IV Curve



Spectral Response



Characteristics

No.	Efficiency(%)	Pmpp(W)	Umpp(V)	Impp(A)	Uoc(V)	Isc(A)
01	19.60	4.79	0.546	8.770	0.641	9.241
02	19.70	4.81	0.548	8.783	0.643	9.264
03	19.80	4.84	0.550	8.796	0.643	9.295
04	19.90	4.86	0.551	8.824	0.644	9.320
05	20.00	4.89	0.553	8.836	0.646	9.332
06	20.10	4.91	0.554	8.864	0.647	9.357
07	20.20	4.94	0.555	8.892	0.648	9.379
08	20.30	4.96	0.556	8.920	0.648	9.420
09	20.40	4.98	0.557	8.940	0.649	9.440
10	20.50	5.01	0.558	8.978	0.649	9.500

Intensity Dependence

Intensidade[w/m2]	Isc	Voc
1000	1.000	1.000
900	0.903	0.996
800	0.803	0.991
600	0.602	0.988
400	0.403	0.962

The short circuit current, open circuit voltage and power at different irradiance intensity.